

CBCS SCHEME

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15EE34

Third Semester B.E. Degree Examination, June/July 2018 Analog Electronic Circuits

Time: 3 hrs.

Max. Marks: 80

Note: Answer any FIVE full questions, choosing one full question from each module.

Module-1

- 1 a. Derive an expression for E_{Th} , I_B and V_{CE} for voltage divider bias circuit using exact analysis. (08 Marks)
- b. For the emitter bias network of Fig.Q1(b), determine the following parameters:
(i) I_B (ii) I_C (iii) V_{CE} (iv) V_C (v) V_E (vi) V_B (vii) V_{BC} (08 Marks)

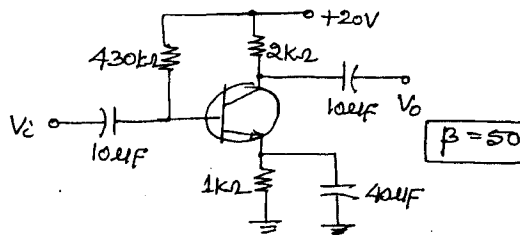


Fig.Q1(b)

OR

- 2 a. Derive the expression for stability factor for fixed bias circuit with respect to I_{CO} , V_{BE} and β . (10 Marks)
- b. With a neat circuit diagram explain the operation of self bias circuit. (06 Marks)

Module-2

- 3 a. With the help of r_e equivalent model, derive an equation for input impedance, output impedance and voltage gain for an emitter follower configuration. (08 Marks)
- b. For the collector feedback configuration having $R_B = 180 \text{ k}\Omega$, $R_C = 2.7 \text{ k}\Omega$, $C_1 = 10 \text{ }\mu\text{F}$, $C_2 = 10 \text{ }\mu\text{F}$, $\beta = 200$, $r_o = \infty \text{ }\Omega$ and $V_{CC} = 9 \text{ volts}$, determine the following parameters:
(i) r_e (ii) Z_i (iii) Z_o (iv) A_v (08 Marks)

OR

- 4 a. High frequency response BJT Amplifier has the following parameters:
 $R_S = 1 \text{ k}\Omega$, $R_1 = 40 \text{ k}\Omega$, $R_2 = 10 \text{ k}\Omega$, $R_E = 2 \text{ k}\Omega$, $R_C = 4 \text{ k}\Omega$, $R_L = 2.2 \text{ k}\Omega$,
 $C_S = 10 \text{ }\mu\text{F}$, $C_C = 1 \text{ }\mu\text{F}$, $C_E = 20 \text{ }\mu\text{F}$, $\beta = 100$, $r_e = 15.76 \text{ }\Omega$, $R_i = 1.32 \text{ k}\Omega$,
 $A_{Vmid}(\text{Amplifier}) = -90$, $r_o = \infty \text{ }\Omega$, $V_{CC} = 20 \text{ V}$, $C_{be} = 36 \text{ pF}$, $C_{bc} = 4 \text{ pF}$, $C_{ce} = 1 \text{ pF}$,
 $C_{wi} = 6 \text{ pF}$, $C_{wo} = 8 \text{ pF}$
(i) Determine f_{Hi} and f_{Ho} . (ii) Determine f_β and f_T (08 Marks)
- b. Derive equations for Miller input capacitance and Miller output capacitance (08 Marks)

Module-3

- 5 a. Derive expressions for Z_i and A_i for a Darlington emitter follower circuit. (10 Marks)
- b. Explain the need of a cascading amplifier? Draw and explain the block diagram of two stage cascade amplifier. (06 Marks)

OR

- 6 a. List the general characteristics of negative feedback amplifiers. (04 Marks)
- b. Determine the voltage gain, input impedance and output impedance with feedback for voltage series feedback amplifier having $A = -100$, $R_i = 10 \text{ k}\Omega$, $R_o = 20 \text{ k}\Omega$ for feedback of (i) $\beta = -0.1$ and (ii) $\beta = -0.5$. (06 Marks)
- c. For a current series feedback amplifier, derive an expression for output impedance with feedback. (06 Marks)

Module-4

- 7 a. With a neat circuit and waveforms, explain the operation of a transformer coupled class-A power amplifier. (08 Marks)
- b. Show that maximum efficiency of class-B push pull power amplifier circuit is 78.54%. (08 Marks)

OR

- 8 a. With a neat circuit diagram and waveform explain the operation of RC phase shift oscillator using BJT. Write the expression for frequency of oscillation. (08 Marks)
- b. With a neat circuit diagram and waveform, explain the working principle of crystal oscillator operating in series resonant mode. A crystal has the following parameters: $L = 0.334 \text{ H}$, $C = 0.065 \text{ PF}$ and $R = 5.5 \text{ k}\Omega$. Calculate the resonant frequency. (08 Marks)

Module-5

- 9 a. Derive the expression for A_v , Z_i and Z_o for a JFET common source amplifier with fixed bias configuration. (08 Marks)
- b. For a self bias JFET circuit, $V_{DD} = +12\text{V}$, $R_D = 2.2 \text{ k}\Omega$, $R_G = 1 \text{ M}\Omega$, $R_S = 1 \text{ k}\Omega$, $I_{DSS} = 8\text{mA}$, $V_P = -4 \text{ volts}$. Determine the following parameters:
(i) V_{GS} (ii) I_D (iii) V_{DS} (iv) V_S (v) V_G (vi) V_D (08 Marks)

OR

- 10 a. Derive expression for V_{GS} , I_D , V_{DS} , V_D and V_S for a voltage divider bias circuit using FET. (08 Marks)
- b. With neat sketches, explain the basic operation and characteristics of n-channel depletion type MOSFET. (08 Marks)
